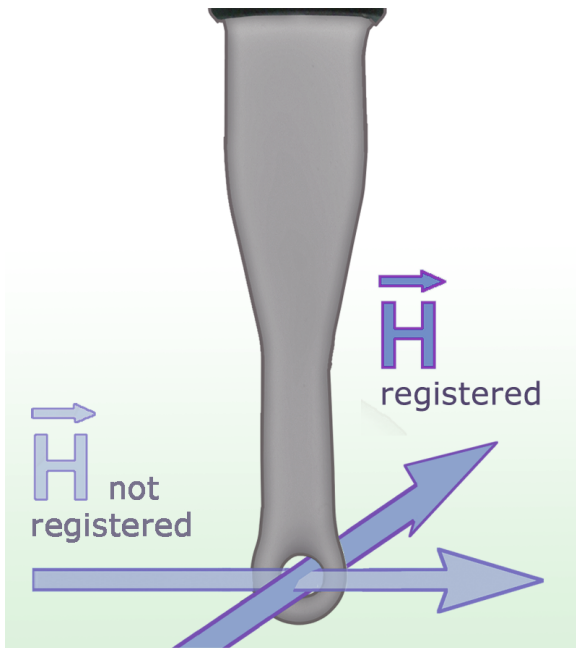


# XF-R 3-1

磁场探头 (30MHz-6GHz)



## Short description

XF-R 3-1型近场探头：用于高分辨率直接检测组件上，譬如IC的引脚或外壳、布线、旁路电容器和电磁兼容性 (EMC) 元件等区域的射频磁场。

In principle the XF-R 3-1 H-field probe has the same structure as the XF-R 100-1 and XF-R 400-1 probes. The resolution of the XF-R 3-1 is significantly higher. The H-field probe is suitable for measurements close to the components with high magnetic field strength. It is not suitable for measurements from large distances, which can be done using XF-R 400-1 and XF-R 100-1. The near-field probe is small and handy. It has a current attenuating sheath and, therefore, is electrically shielded. It can be connected to a spectrum analyzer or an oscilloscope with a 50  $\Omega$  input. The H-field probe has an internal terminating resistance.

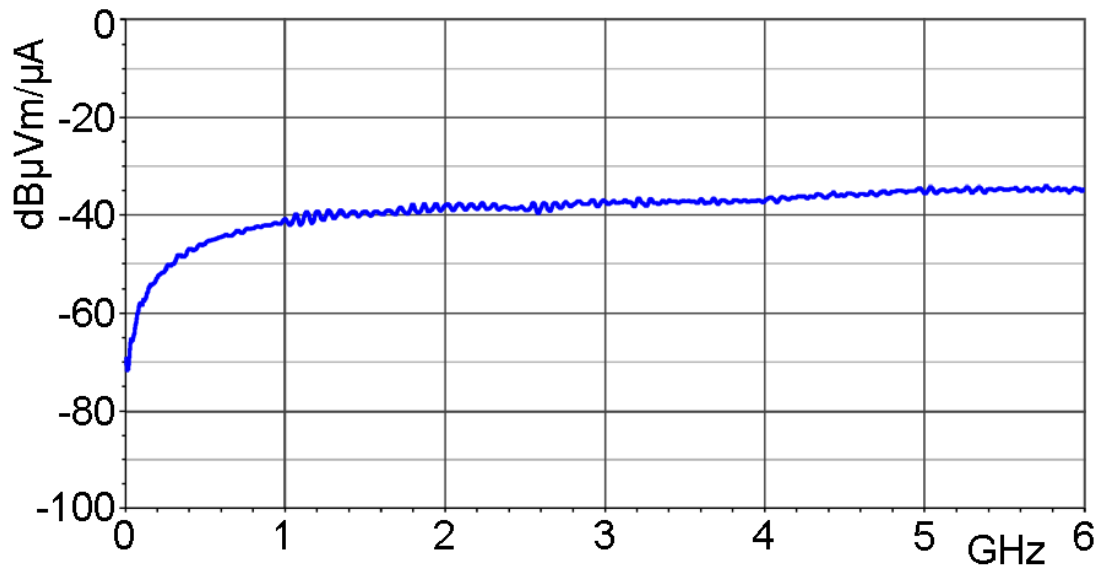
## Technical parameters

频率范围	30 MHz ... 6 GHz
分辨率	$\approx 1$ mm
探头尺寸	$\varnothing \approx 3$ mm
输出接口	SMA, female, jack
重量	15 g

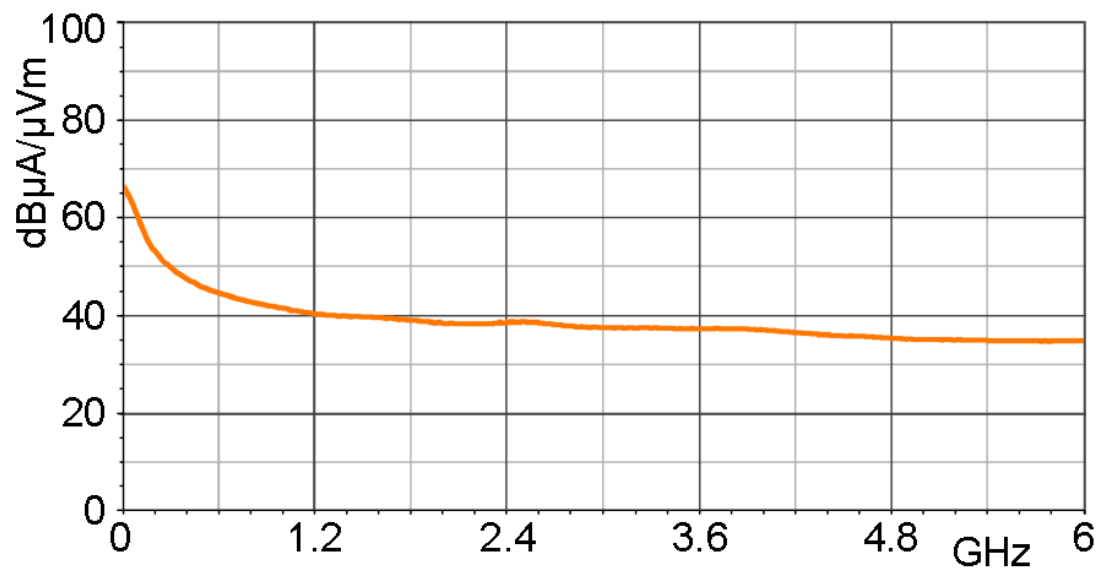
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频率特性 [dB $\mu$ V] / [dB $\mu$ A/m]



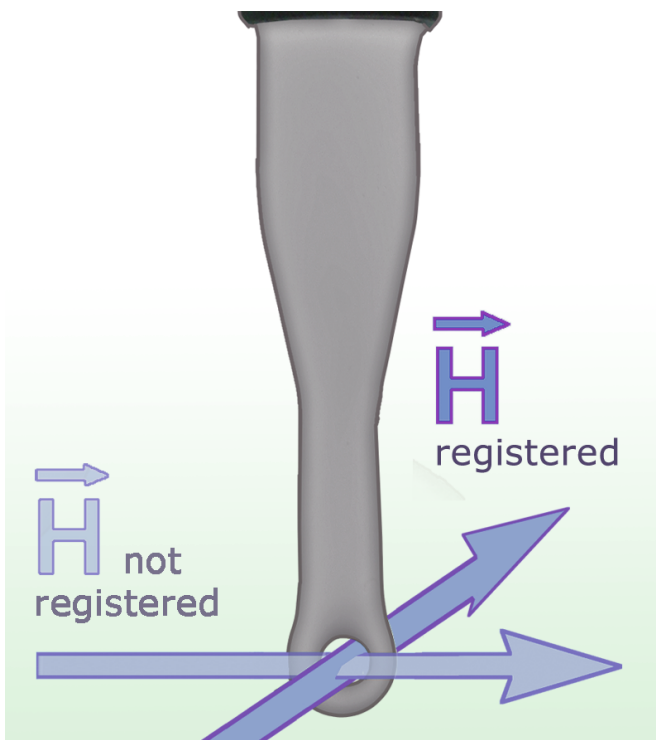
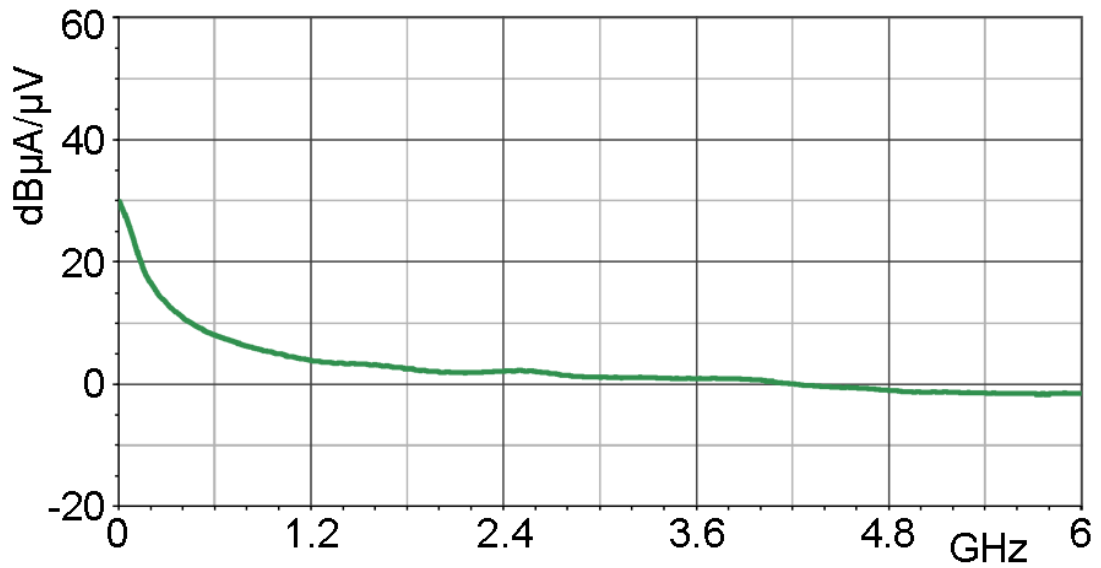
磁场校正曲线 [dB $\mu$ A/m] / [dB $\mu$ V]



# XF-R 3-1

磁场探头 (30MHz-6GHz)

电流校正曲线 [dB $\mu$ A] / [dB $\mu$ V]



# XF-R 3-1

磁场探头 (30MHz-6GHz)

Probe head

